

N-Channel Enhancement Mode Field Effect Transistor

- 60Amp 60Volt

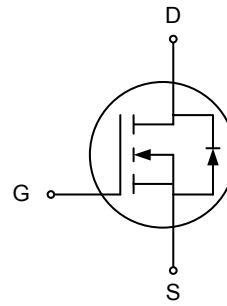
Application

- Servomotor control
- Power MOSFET gate drivers
- Other switching applications

Feature

- Small surface mounting type
- High density cell design for low RDS(ON)
- Suitable for high packing density
- Rugged and reliable
- High saturation current capability
- Voltage controlled small signal switch

Circuit



Construction

- N-Channel Enhancement

Absolute Maximum Ratings

PARAMETER	SYMBOL	PS60N60	UNIT
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	± 20	V
Drain Current-Continuous @ TA = 125°C (Note 1)	I _D	60	A
	-Pulsed (Note 2)	I _{DM}	
Drain-Source Diode Forward Current	I _S	60	A
Maximum Power Dissipation	P _D	110	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

Note: 1.Surface Mounted on FR-4 Board, t ≤ 2%

June 2009 / Rev.6.4

2.Pulse Test : 380µs pulse width, 2% duty cycle

Electrical Characteristics

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BVDSS	VGS = 0V, ID = -250μA	60	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS = 20V, VGS = 0V	-	-	1	μA
Gate-Body Leakage	IGSS	VGS = ±16V, VDS = 0V	-	-	±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = -250μA	2	-	4	V
Static Drain-Source On-Resistance	RDS(on)	VGS = 10V, ID = 60A	-	16	18	mΩ
		VGS = 4.5V, ID = 30A	-	20	23	
Forward Transconductance	gFS	VDS = 25V, ID = 30A	-	50	-	S
SWITCHING CHARACTERISTICS						
Total Gate Charge	Qg	VDS = 30V, ID = 60A VGS = 10V, RGEN = 4.7Ω	-	54	75	nC
Gate-Source Charge	Qgs		-	10	-	
Gate-Drain Charge	Qgd		-	20	-	
Turn-On Delay Time	TD(on)	VDD = 30V, ID = 30A VGEN = 10V, RL = 10Ω RGEN = 4.7Ω	-	15	-	nS
Rise Time	tr		-	60	-	
Turn-Off Delay Times	TD(off)		-	40	-	nS
Fall Time	tf		-	16	-	
DYNAMIC CHARACTERISTICS						
Input Capacitance	Ciss	VDS = 10V, VGS = 0V f = 1.0MHz	-	1700	-	pF
Output Capacitance	Coss		-	400	-	
Reverse Transfer Capacitance	Crss		-	135	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage	VSD	VGS = 0V, IS = 60A	-	1.5	-	V

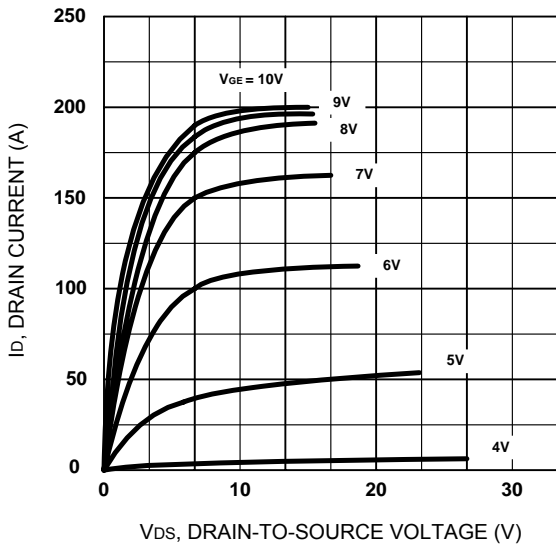


Figure 1. Output Characteristics

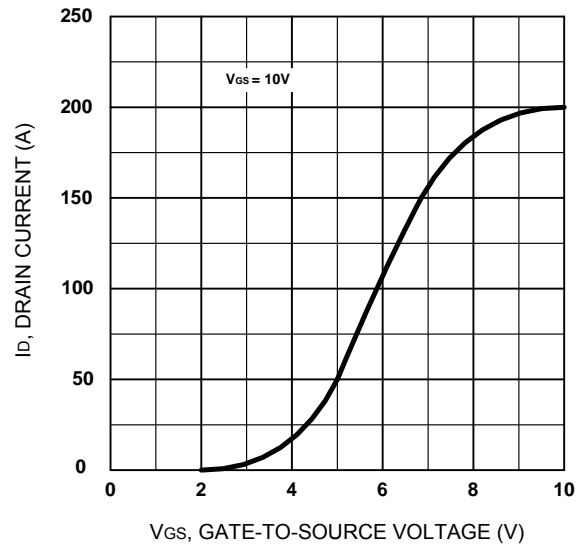


Figure 2. Transfer Characteristics

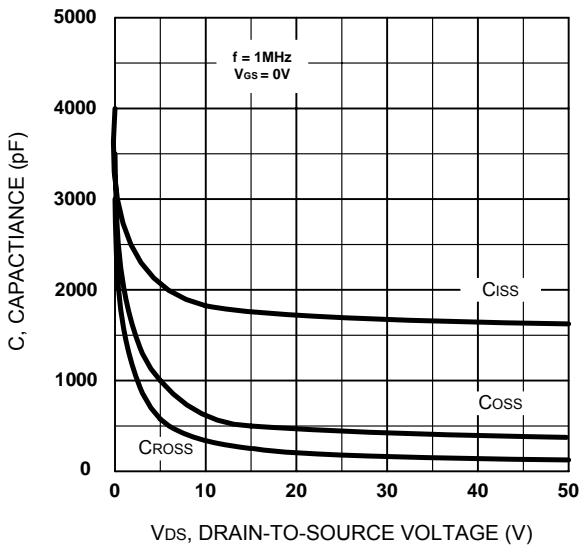


Figure 3. Capacitance Characteristics

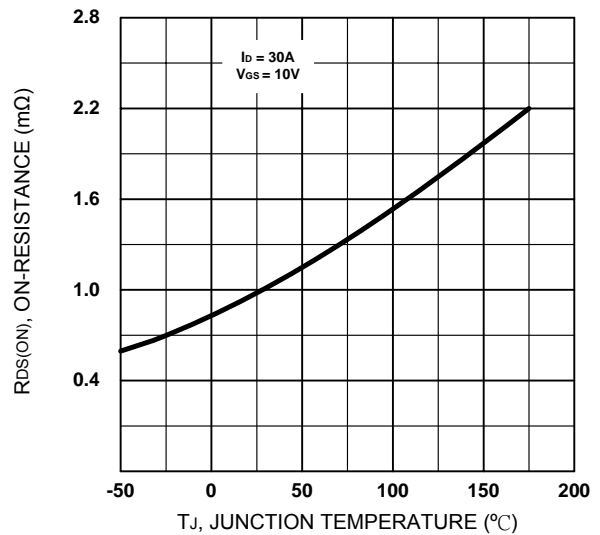


Figure 4. On-Resistance Variation with temperature

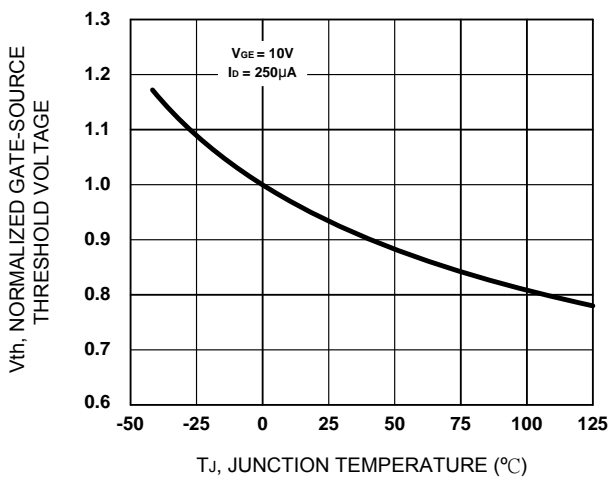


Figure 5. Gate Threshold Variation with Temperature

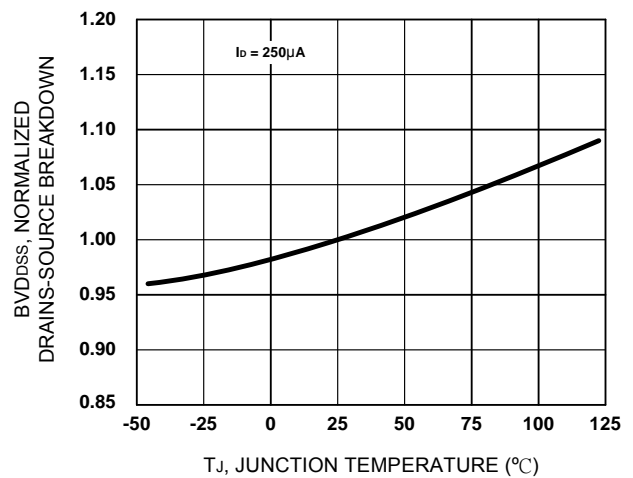


Figure 6. Breakdown Voltage Variation with Temperature

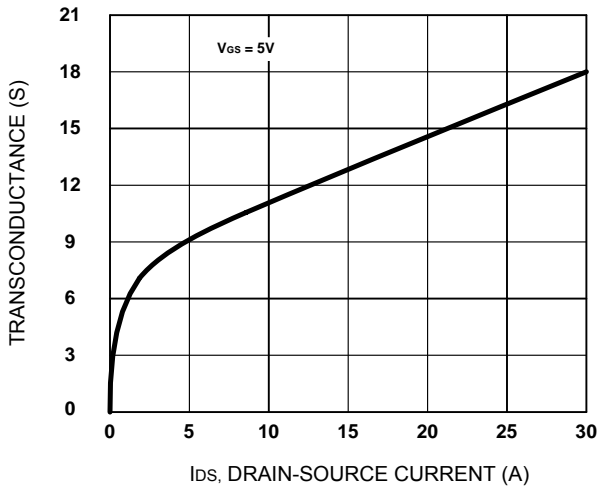


Figure 7. Transconductance Variation with Drain Current

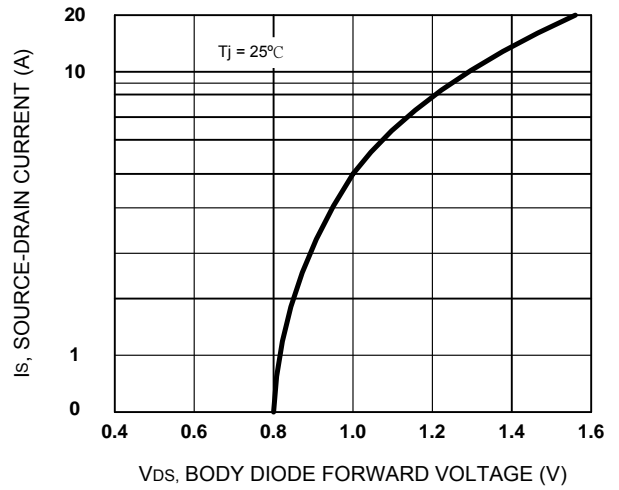


Figure 8. Body Diode Forward Voltage Variation with Source Current

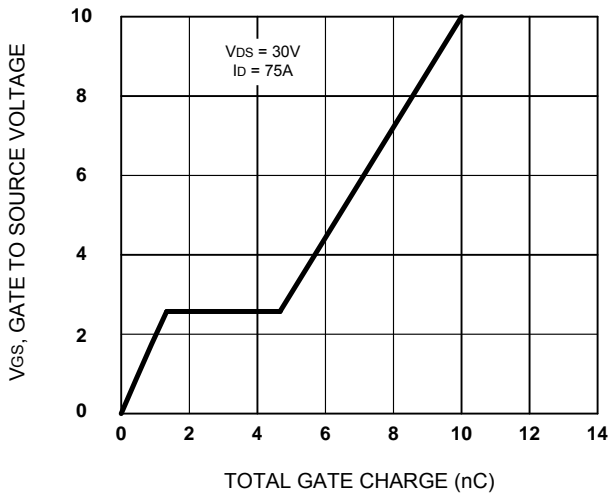
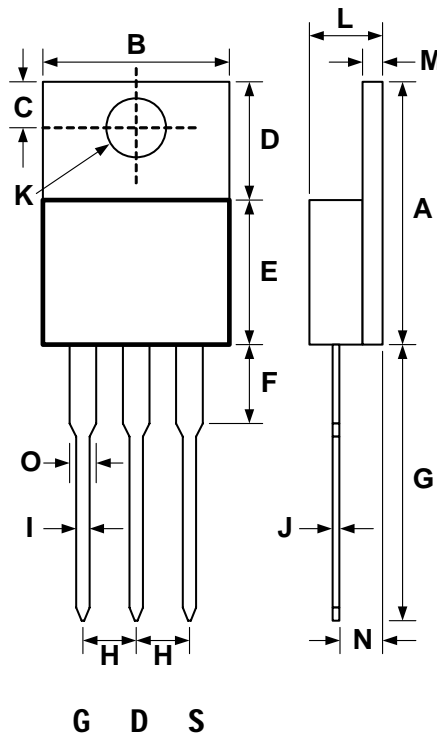


Figure 9. Gate Charge

TO-220AB PACKAGE



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.579	.606	14.70	15.40	
B	.392	.411	9.95	10.45	
C	.104	.116	2.65	2.95	
D	.248	.272	6.30	6.90	
E	.325	.350	8.25	8.90	
F	.126	.157	3.20	4.00	
G	.492	.551	12.50	14.00	
H	.096	.108	2.45	2.75	
I	.028	.039	0.70	1.00	
J	.010	.022	0.25	0.55	
K	.146	.157	3.70	4.00	
L	.167	.187	4.25	4.75	
M	.045	.057	1.15	1.45	
N	.089	.114	2.25	2.90	
O	.047	.055	1.20	1.40	



Sirectifier Global Corp., Delaware, U.S.A.

U.S.A.: sgc@sirectsemi.com France: ss@sirectsemi.com Taiwan: se@sirectsemi.com Hong Kong: hk@sirectsemi.com
 China: st@sirectsemi.com Thailand: th@sirectsemi.com Philippines: aiac@sirectsemi.com Belize: belize@sirectsemi.com